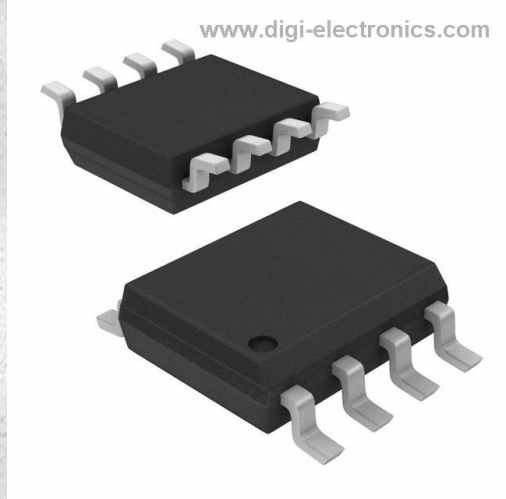
FAN7527BM Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	FAN7527BM-DG
Manufacturer	onsemi
Manufacturer Product Number	FAN7527BM
Description	IC PFC CTRLR TRANSITION 8SOP
Detailed Description	PFC IC Discontinuous (Transition) 8-SOIC

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FAN7527BM	onsemi
Series:	Product Status:
-	Obsolete
Mode:	Frequency - Switching:
Discontinuous (Transition)	-
Current - Startup:	Voltage - Supply:
60 µA	11.5V ~ 30V
Operating Temperature:	Mounting Type:
-25°C ~ 125°C	Surface Mount
Package / Case:	Supplier Device Package:
8-SOIC (0.154", 3.90mm Width)	8-SOIC
Base Product Number:	
FAN7527	

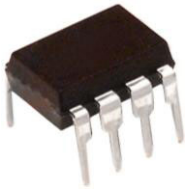
Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8542.39.0001

DATA SHEET
www.onsemi.com

Power Factor Correction Controller

FAN7527B



PDIP8 9.42x6.38, 2.54P
CASE 646CM

SOIC8
CASE 751EB

Description

The FAN7527B provides simple and high−performance active Power Factor Correction (PFC). The FAN7527B is optimized for electronic ballasts and low−power, high−density power supplies that require minimum board size, reduced external components, and low power dissipation. Because the R/C filter is included in the current−sense block, an external R/C filter is not necessary. Special circuitry prevents no−load runaway conditions. Regardless of the supply voltage, the output drive clamping circuit limits the overshoot of the power MOSFET gate drive, which improves system reliability.

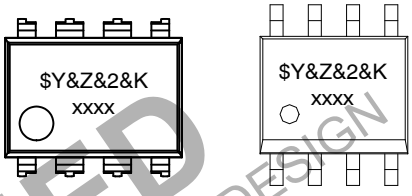
Features

- Internal Startup Timer
- Internal R/C Filter Eliminates the Need for External R/C Filter
- Precise Adjustable Output Over−Voltage Protection
- Zero Current Detector
- One Quadrant Multiplier
- Trimmed 1.5% Internal Band Gap Reference
- Under−Voltage Lockout with 3 V of Hysteresis
- Totem−Pole Output with High−State Clamp
- Low Startup and Operating Current
- 8−Pin SOP or 8−Pin DIP
- These Devices are Pb−Free and are RoHS Compliant

Applications

- Electronic Ballast
- SMPS

MARKING DIAGRAM



$Y = **onsemi** Logo
&Z = Assembly Plant Code
&2 = 2−Digit Date Code
&K = Lot Run Traceability Code
xxxx = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
FAN7527BN	PDIP8 (Pb−Free)	3000 / Tube
FAN7527BMX	SOIC8 (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NOTE: Operating Temperature Range of both devices is −25 to +125°C

FAN7527B

BLOCK DIAGRAM

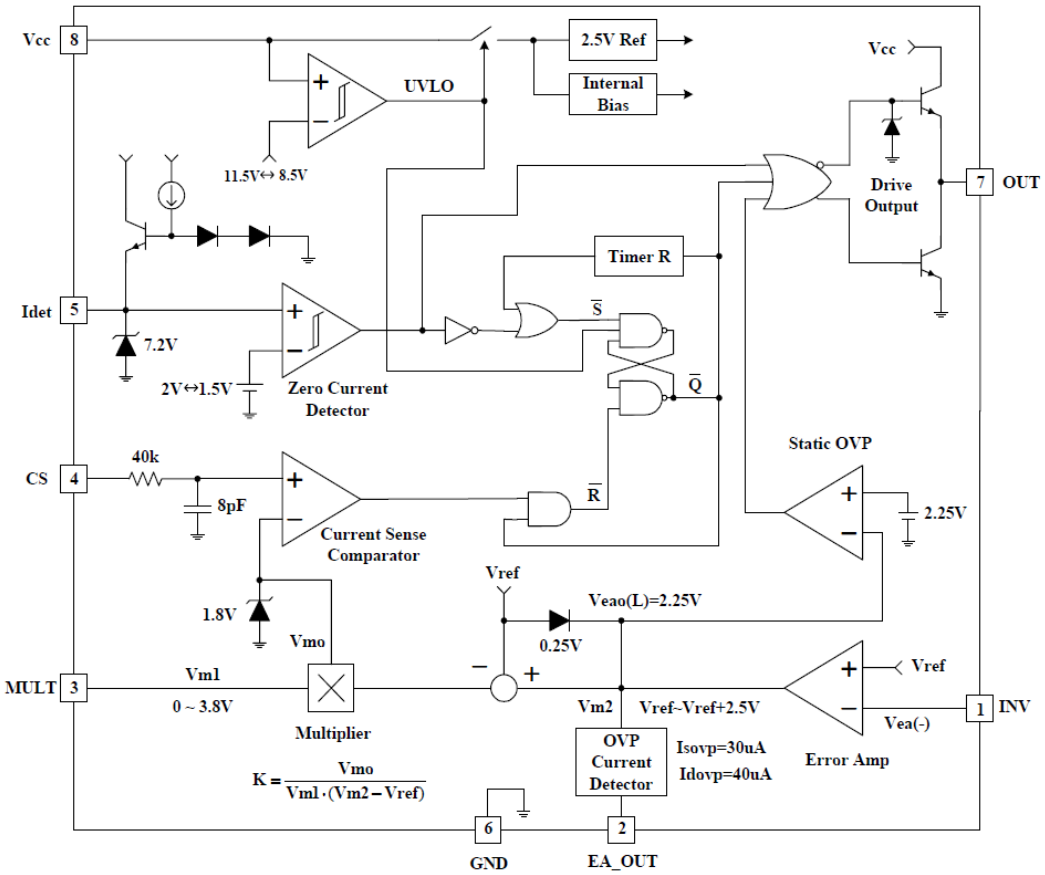


Figure 1. Block Diagram

FAN7527B

PIN CONFIGURATION

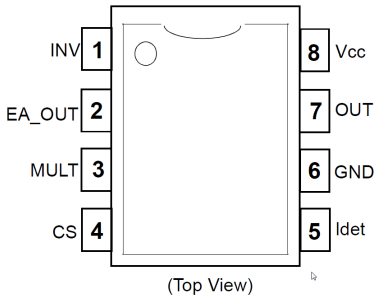


Figure 2. Pin Configuration

PIN DEFINITIONS

Pin #	Name	Description
1	INV	Inverting input of the error amplifier. The output of the boost converter should be resistively divided to 2.5 V and connected to this pin.
2	EA_OUT	Output of the error amplifier. Feedback compensation network is placed between this pin and the INV pin.
3	MULT	Input to the multiplier stage. The full−wave rectified AC voltage is divided to less than 2 V and is connected to this pin.
4	CS	Input of the PWM comparator. The MOSFET current is sensed by a resistor and the resulting voltage is applied to this pin. An internal R/C filter is included to reject high−frequency noise
5	Idet	Zero Current Detection (ZCD) input
6	GND	Ground
7	OUT	Gate driver output. Push−pull output stage is able to drive the power MOSFET with a peak current of 500 mA
8	V_{CC}	Supply voltage of driver and control circuits

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Min.	Max.	Unit
V_{CC}	Supply Voltage			30	V
I_{OH}, I_{OL}	Peak Drive Output Current			±500	mA
I_{CLAMP}	Driver Output Clamping Diodes $V_O > V_{CC}$ or $V_O < -0.3$ V			±10	mA
I_{DET}	Detector Clamping Diodes			±10	mA
V_{IN}	Error Amplifier Multiplier and Comparator Input Voltages		−0.3	6.0	V
T_J	Operation Junction Temperature			+150	°C
T_{OPR}	Operating Temperature Range		−25	+125	°C
T_{STG}	Storage Temperature Range		−65	+150	°C
P_D	Power Dissipation	SOIC8		0.8	W
		PDIP8		1.1	W
Θ_{JA}	Thermal Resistance Junction−Ambient	SOIC8		150	°C/W
		PDIP8		110	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

TEMPERATURE CHARACTERISTICS

(−25°C ≤ T_A ≤ 125°C)

Symbol	Parameter	Min.	Typ.	Max.	Unit
ΔV_{REF}	Temperature Stability Reference Voltage (V_{REF})		20		mV
$\Delta K/\Delta T$	Temperature Stability for Multiplier Gain (K)		−0.2		% / °C

ELECTRICAL CHARACTERISTICS

(V_{CC} = 14 V, −25°C ≤ T_A ≤ 125°C, unless otherwise stated.)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
UNDER−VOLTAGE LOCKOUT						
$V_{th(st)}$	Start Threshold Voltage	V_{CC} Increasing	10.5	11.5	12.5	V
$H_{Y(st)}$	UVLO Hysteresis		2	3	4	V
SUPPLY CURRENT SECTION						
I_{ST}	Startup Supply Current	V_{CC} = $V_{th(st)}$ −0.2 V	10	60	100	μA
I_{CC}	Operating Supply Current	Output Not Switching		3	6	mA
$I_{CC(OVP)}$	Operating Current at OVP	V_{INV} = 3 V		1.7	4.0	mA
I_{DCC}	Dynamic Operating Supply Current	50 kHz, C_l = 1 nF		4	8	mA
ERROR AMPLIFIER SECTION						
V_{REF}	Voltage Feedback Input Threshold	I_{REF} = 0 mA, T_A = 25°C	2.465	2.500	2.535	V
		25°C ≤ T_A ≤ 125°C	2.440	2.500	2.560	
ΔV_{FEF1}	Line Regulation	14 V ≤ V_{CC} ≤ 25 V		0.1	10.0	mV
ΔV_{FEF3}	Temperature Stability of V_{REF} (Note 1)	−25°C ≤ T_A ≤ 125°C		20		mV
$I_{b(ea)}$	Input Bias Current		−0.5		0.5	μA
I_{SOURCE}	Output Source Current	V_{M2} = 4 V	−2	−4		mA
I_{SINK}	Output Sink Current	V_{M2} = 4 V	2	4		mA
$V_{EAO(H)}$	Output Upper Clamp Voltage (Note 1)	I_{SOURCE} = 0.1 mA		6		V
$V_{EAO(L)}$	Output Lower Clamp Voltage (Note 1)	I_{SINK} = 0.1 mA		2.25		V
G_V	Large Signal Open−Loop Gain (Note 1)		60	80		dB
PSRR	Power Supply Rejection Ratio (Note 1)	14 V ≤ V_{CC} ≤ 25 V	60	80		dB
GBW	Unity Gain Bandwidth (Note 1)			1		MHz
SR	Slew Rate (Note 1)			0.6		V/μs
MULTIPLIER SECTION						
$I_{b(m)}$	Input Bias Current (Pin 3)		−0.5		0.5	μA
ΔV_{M1}	M1 Input Voltage Range (Pin 3)				3.8	V
ΔV_{M2}	M2 Input Voltage Range (Pin 2)		V_{REF}		V_{REF}+2.5	V
K	Multiplier Gain (Note 1)	V_{M1} = 1 V, V_{M2} = 3.5 V	0.36	0.44	0.52	1 / V
$V_{OMAX(m)}$	Maximum Multiplier Output Voltage	V_{INV} = 0 V, V_{M1} = 4 V	1.65	1.80	1.95	V
ΔK/ΔT	Temperature Stability of K (Note 1)	−25°C ≤ T_A ≤ 125°C		−0.2		% / °C
CURRENT SENSE SECTION						
$V_{IO(CS)}$	Input Offset Voltage (Note 1)	V_{M1} = 0 V, V_{M2} = 2.2 V	−10	3	10	mV
$I_{b(CS)}$	Input Bias Current	0 V ≤ V_{CS} ≤ 1.7 V	−1.0	−0.1	1.0	μA
$t_{D(CS)}$	Current Sense Delay to Output (Note 1)			200	500	ns
ZERO CURRENT DETECT SECTION						
$V_{TH(DET)}$	Input Voltage Threshold	V_{DET} Increasing	1.7	2.0	2.3	V
$H_{Y(DET)}$	Detect Hysteresis		0.2	0.5	0.8	V
$V_{CLAMP(I)}$	Input Low Clamp Voltage	I_{DET} = −100 μA	0.45	0.75	1.00	V
$V_{CLAMP(H)}$	Input High Clamp Voltage	I_{DET} = 3 mA	6.5	7.2	7.9	V

ELECTRICAL CHARACTERISTICS (continued)
(V_{CC} = 14 V, −25°C ≤ T_A ≤ 125°C, unless otherwise stated.)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
ZERO CURRENT DETECT SECTION						
$I_{b(DET)}$	Input Bias Current	1 V ≤ V_{DET} ≤ 5 V	−1.0	−0.1	1.0	μA
$I_{CLAMP(D)}$	Input High/Low Clamp Diode Current (Note 1)				±3	mA
OUTPUT SECTION						
V_{OH}	Output Voltage High	I_O = −10 mA	10.5	11.0		V
V_{OL}	Output Voltage Low	I_O = 10 mA		0.8	1.0	V
t_R	Rising Time (Note 1)	C_L = 1 nF		130	200	ns
t_F	Falling Time (Note 1)	C_L = 1 nF		50	120	ns
$V_{OMAX(O)}$	Maximum Output Voltage	V_{CC} = 20 V, I_O = 100 μA	12	14	16	V
$V_{OMIN(O)}$	Output Voltage with UVLO Activated	V_{CC} = 5 V, I_O = 100 μA			1	V
RESTART TIMER SECTION						
$t_{D(RST)}$	Restart Time Delay	V_{M1} = 1 V, V_{M2} = 3.5 V		150		μs
OVER−VOLTAGE PROTECTION SECTION						
I_{SOVP}	Soft OVP Detecting Current		25	30	35	μA
I_{DOVP}	Dynamic OVP Detecting Current		35	40	45	μA
V_{OVP}	Static OVP Threshold Voltage	V_{INV} = 2.7 V	2.10	2.25	2.40	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. These parameters, although guaranteed, are not 100% tested in production.

Multiplier Gain:

$$K = \frac{Pin4\_Threshold}{V_{M1} \times (V_{M2} - V_{REF})}$$

where $V_{M1} = V_{PIN3}$, $V_{M2} = V_{PIN2}$

TYPICAL PERFORMANCE CHARACTERISTICS

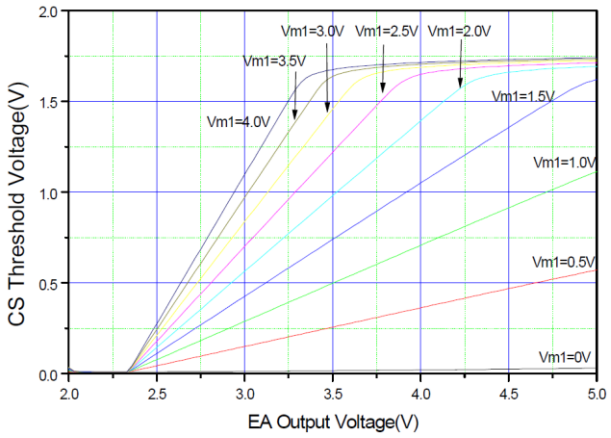


Figure 3. Error Amplifier Output Voltage vs. Current Sensing Threshold

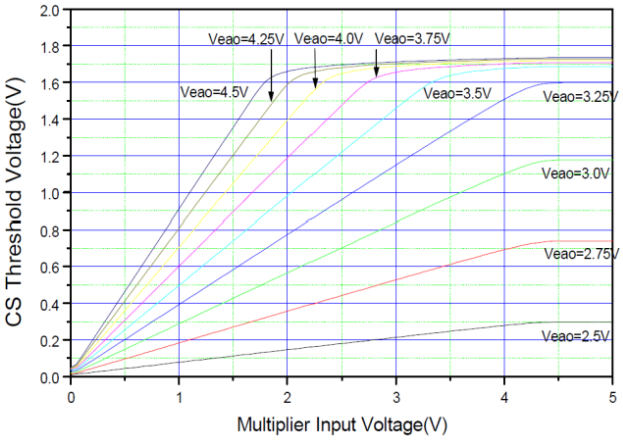


Figure 4. Multiplier Input Voltage vs. Current Sensing Threshold

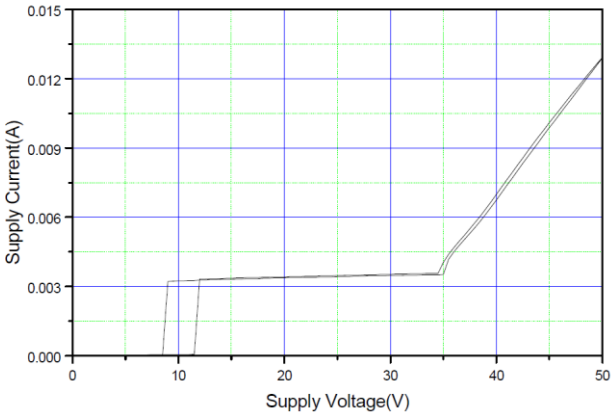


Figure 5. Supply Current vs. Supply Voltage

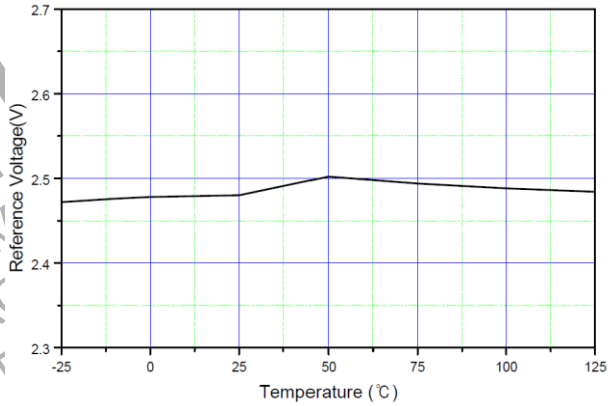


Figure 6. Reference Voltage vs. Temperature

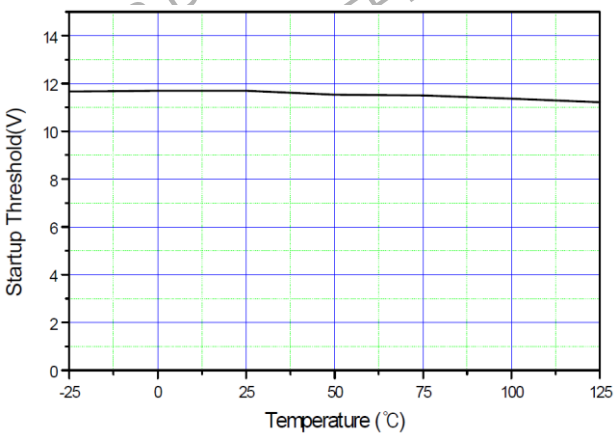


Figure 7. Startup Threshold vs. Temperature

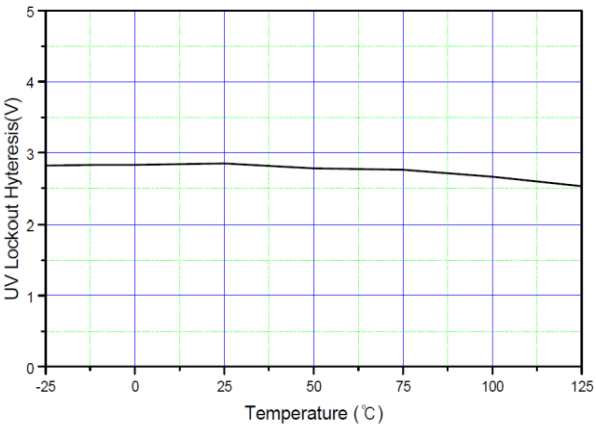


Figure 8. UVLO Hysteresis vs. Temperature

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

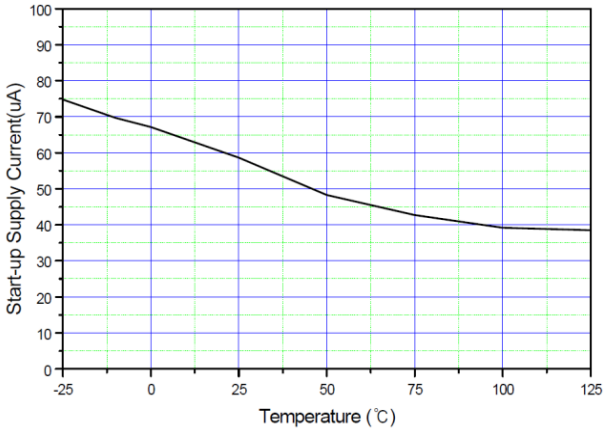


Figure 9. Startup Supply Current vs. Temperature

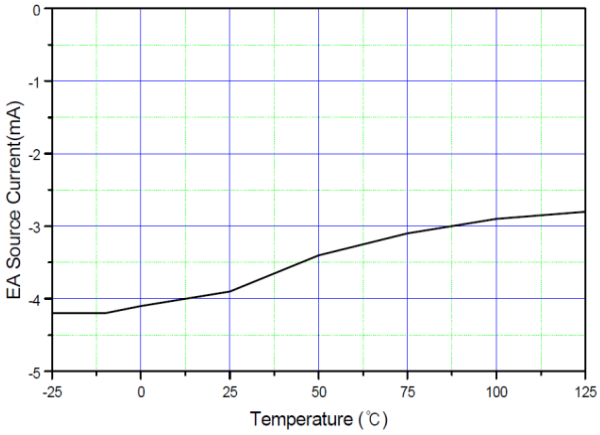


Figure 10. Error Amplifier Source Current

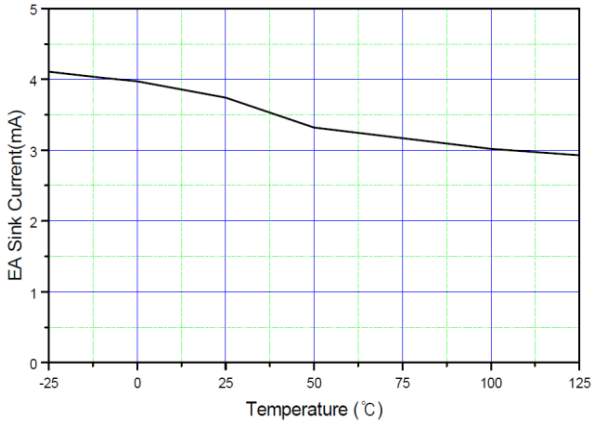


Figure 11. Error Amplifier Sink Current vs. Temperature

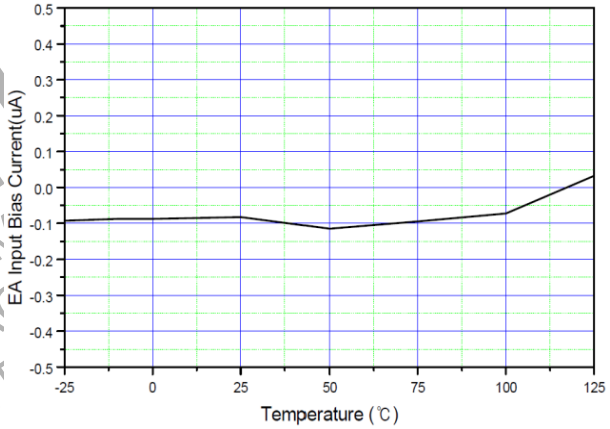


Figure 12. Error Amplifier Input Bias Current vs. Temperature

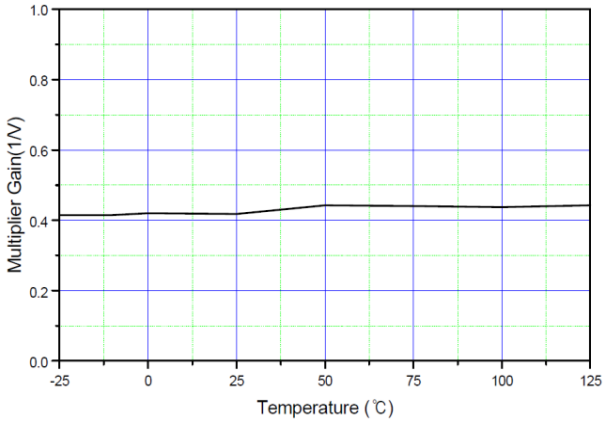


Figure 13. Multiplier Gain vs. Temperature

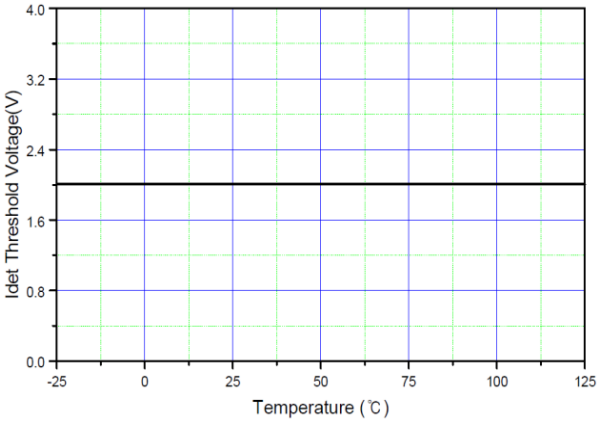


Figure 14. I_{DET} Threshold Voltage vs. Temperature

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

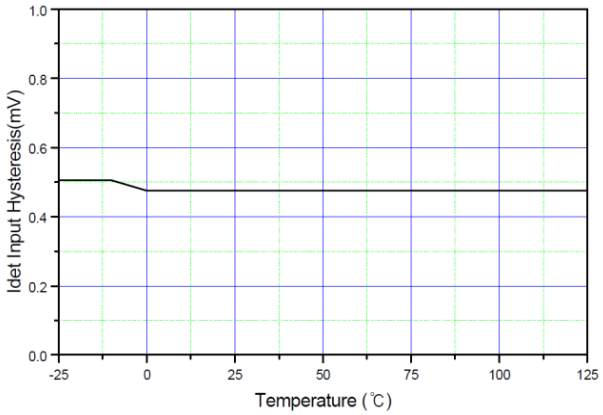


Figure 15. IDET Input Hysteresis vs. Temperature

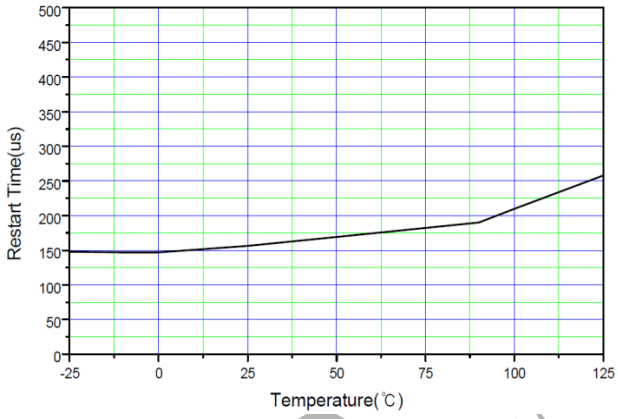


Figure 16. Restart Time vs. Temperature

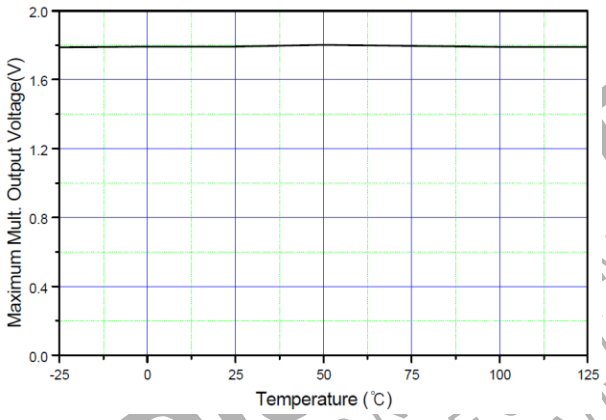


Figure 17. Maximum Multiplier Output Voltage vs. Temperature

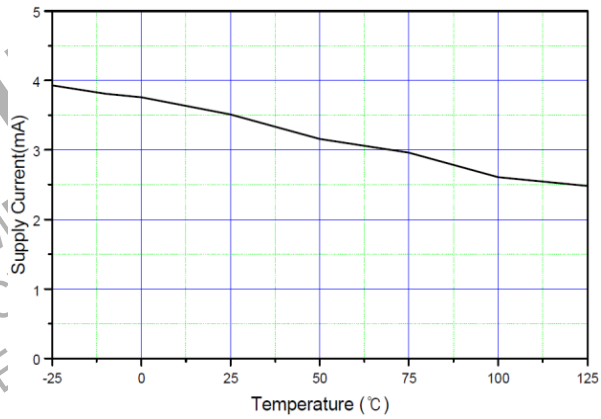


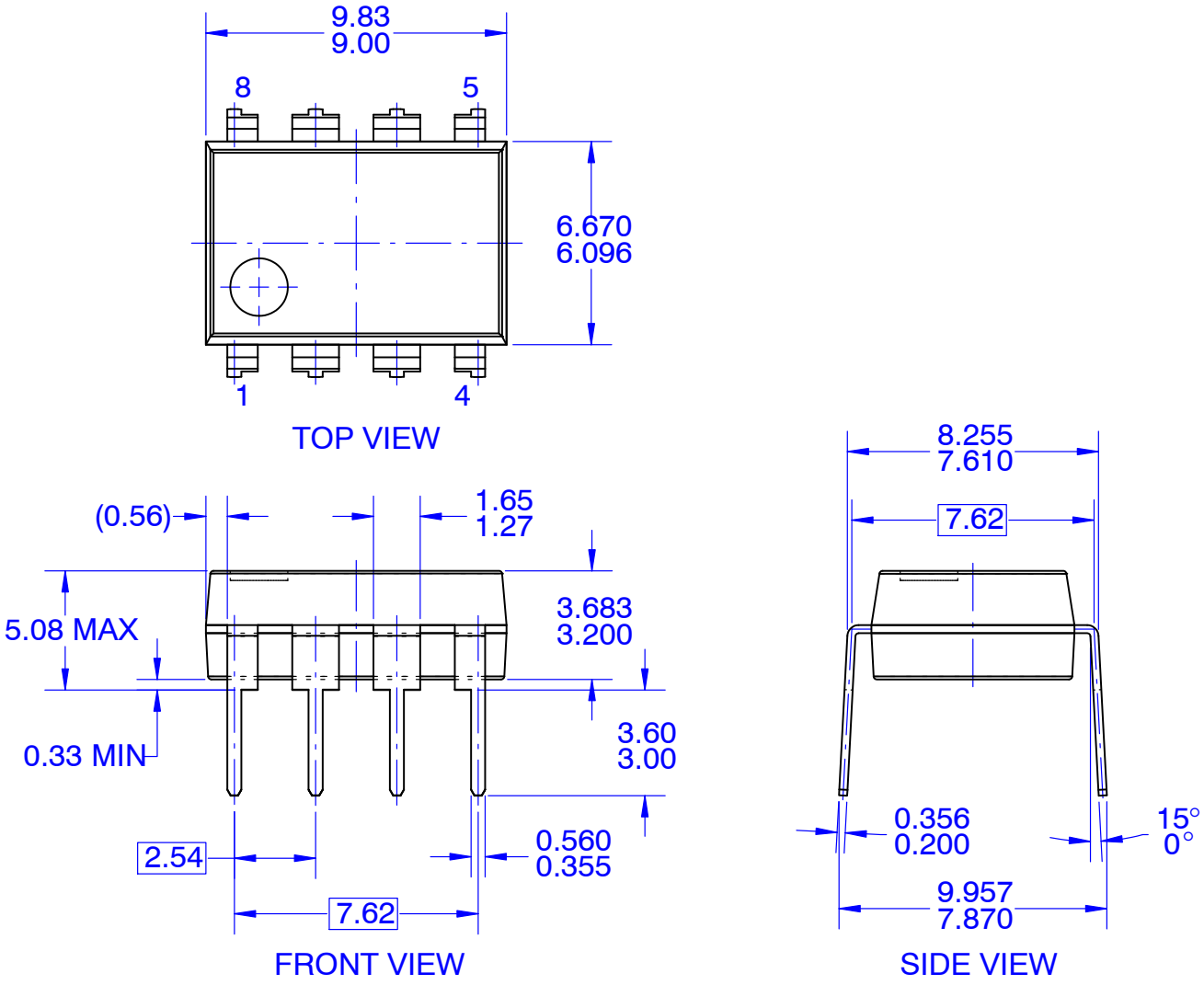
Figure 18. Supply Current vs. Temperature

onsemi

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

PDIP8 9.42x6.38, 2.54P
CASE 646CM
ISSUE O

DATE 31 JUL 2016



NOTES:
A. CONFORMS TO JEDEC MS−001, VARIATION BA
B. ALL DIMENSIONS ARE IN MILLIMETERS
C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS
D. DIMENSIONS AND TOLERANCES PER ASME Y14.5M−2009

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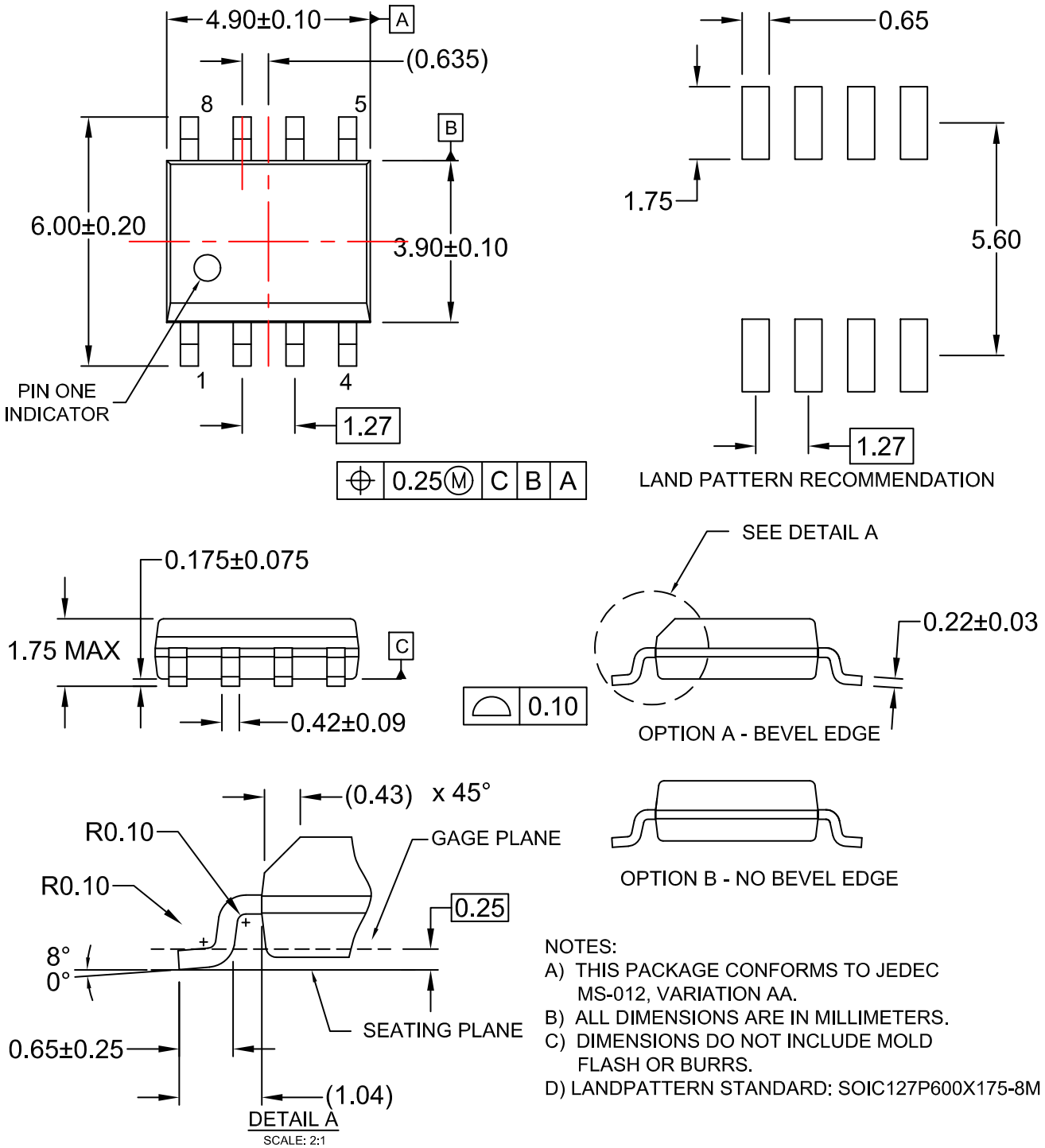
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

SOIC8
CASE 751EB
ISSUE A

DATE 24 AUG 2017



NOTES:
A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
D) LANDPATTERN STANDARD: SOIC127P600X175-8M

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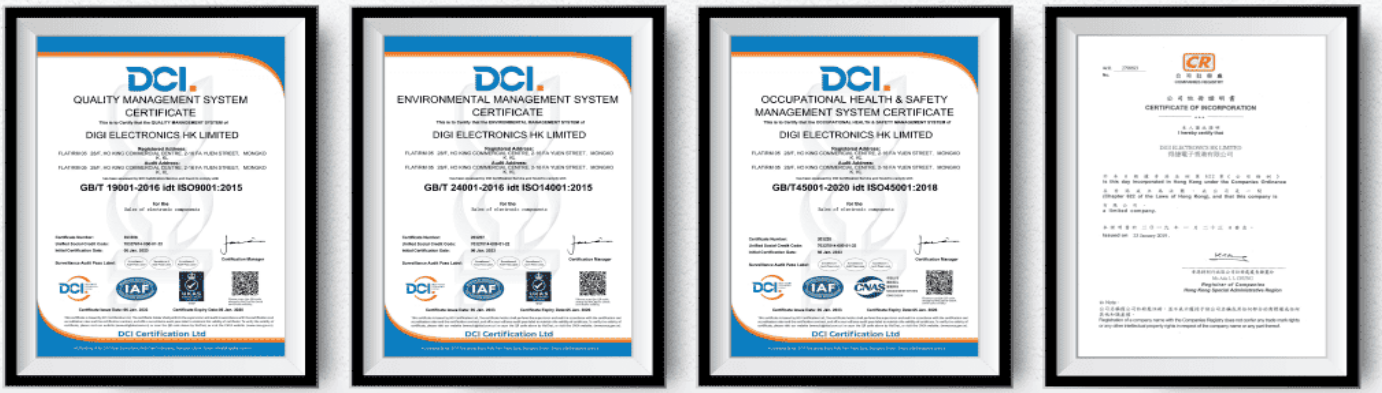

Tel: +00 852-30501935

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